TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK2013

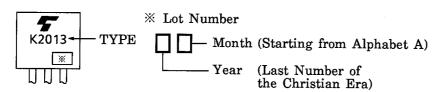
Audio Frequency Power Amplifier Application

- High breakdown voltage $: V_{DSS} = 180V$
- High forward transfer admittance $|Y_{fs}| = 0.7 \text{ S (typ.)}$
- Complementary to 2SJ313

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage	V _{DSS}	180	V	
Gate-source voltage	V _{GSS}	±20	V	
Drain current (Note 1)	Ι _D	1	А	
Drain power dissipation (Tc = 25°C)	PD	25	W	
Channel temperature	T _{ch}	150	°C	
Storage temperature range	T _{stg}	-55~150	°C	

Marking



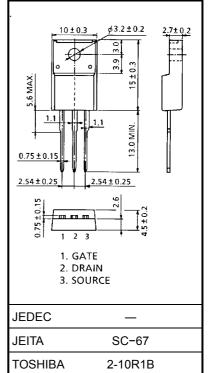
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{DS} = 0, V_{GS} = ±20 V	_	_	±100	nA
Drain-source breakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0	180	_	_	V
Gate-source cut-off voltage (Note 2)	V _{GS (OFF)}	V _{DS} = 10 V, I _D = 10 mA	1.8		2.8	V
Drain-source saturation voltage	V _{DS (ON)}	I _D = 0.6 A, V _{GS} = 10 V	_	1.7	3.0	V
Forward transfer admittance	Y _{fs}	V _{DS} = 10 V, I _D = 0.3 A	_	0.7	_	S
Input capacitance	C _{iss}	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz	_	170	_	
Output capacitance	C _{oss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		45	_	pF
Reverse transfer capacitance	C _{rss}	V _{DD} ≈ 10 V, V _{GS} = 0, f = 1 MHz	_	17	_	

Note 1: Please use devices on condition that the channel temperature is below 150°C.

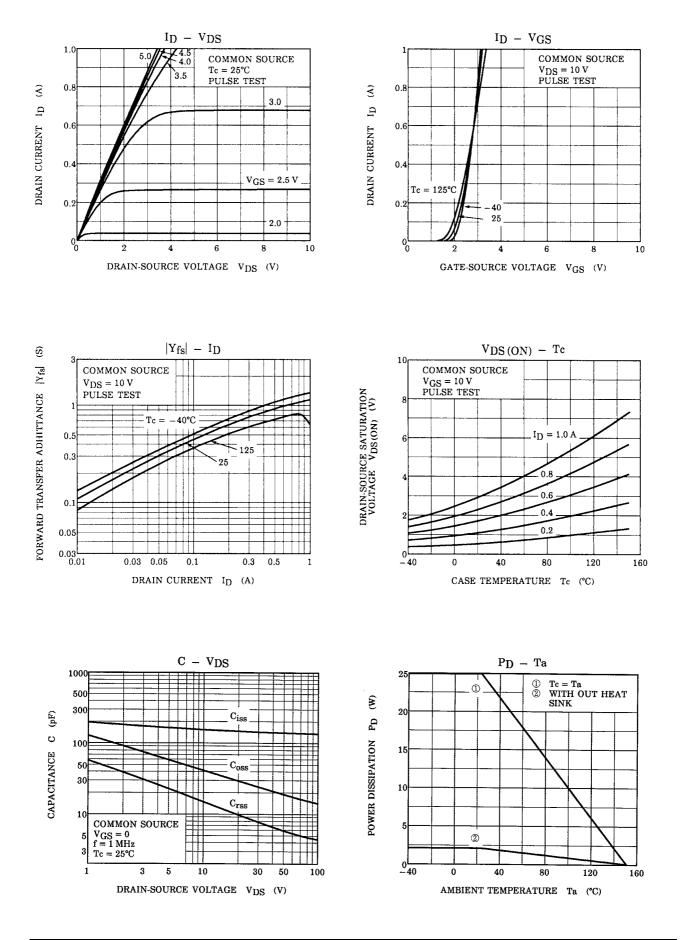
Note 2: V_{GS (OFF)} Classification O: 0.8~1.6, Y: 1.4~2.8

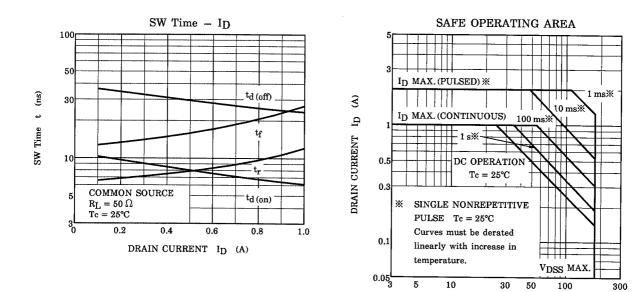
This transistor is the electrostatic sensitive device. Please handle with caution.



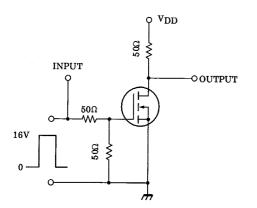
Weight: 1.9 g (typ.)

Unit: mm

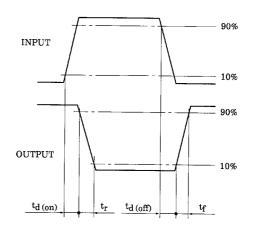




Switching Time Test Circuit



Waveforms



DRAIN-SOURCE VOLTAGE VDS (V)

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